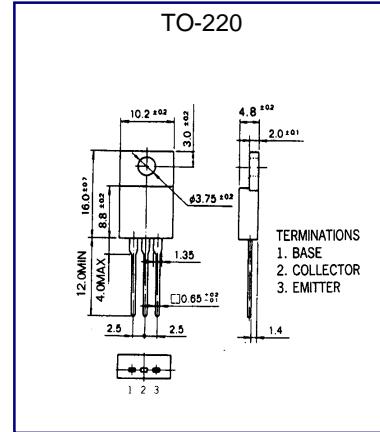




**BU406/406H/408**

**NPN EPITAXIAL SILICON TRANSISTOR**

**HIGH VOLTAGE SWITCHING USE IN  
HORIZONTAL DEFLECTION OUTPUT STAGE**



**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	400	V
Collector-Emitter Voltage	V <sub>CE0</sub>	200	V
Emitter-Base voltage	V <sub>EB0</sub>	6	V
Collector Current (DC)	I <sub>C</sub>	7	A
Collector Peck Current	I <sub>CM</sub>	10	A
Base Current (DC)	I <sub>B</sub>	4	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	60	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-65~150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit	
Collector Cutoff Current (V <sub>BE</sub> =0)	I <sub>CES</sub>	V <sub>CE</sub> = 400V , V <sub>EB</sub> = 0			5	mA	
		V <sub>CE</sub> = 250V , V <sub>EB</sub> = 0			100	μA	
		V <sub>CE</sub> = 250V , V <sub>EB</sub> = 0			1	mA	
Emitter Cutoff Current(I <sub>C</sub> =0)	I <sub>EBO</sub>	V <sub>CE</sub> = 250V , V <sub>EB</sub> = 0			1	mA	
Collector Emitter Saturation Voltage :BU406 :BU406H :BU408	V <sub>CE(sat)</sub>	T <sub>c</sub> =150			1	V	
		V <sub>EB</sub> = 6V , I <sub>C</sub> =0			1	V	
		I <sub>C</sub> =5A, I <sub>B</sub> =0.5A			1.2	V	
Base- Emitter Saturation Voltage :BU406 :BU406H :BU408	V <sub>BE(sat)</sub>	I <sub>C</sub> =5A, I <sub>B</sub> =0.8A			1.2	V	
		I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			1.5	V	
		I <sub>C</sub> =5A, I <sub>B</sub> =0.5A					
Current Gain Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> =5A, I <sub>B</sub> =0.5A	10			MHZ	
Turn-Off Time :BU406 :BU406H :BU408	t <sub>off</sub>	I <sub>C</sub> =5A, I <sub>B</sub> =0.8A			0.75	μS	
		I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			0.4	μS	
		V <sub>CE</sub> = 10V , I <sub>C</sub> =500mA			0.4	μS	
		I <sub>C</sub> =5A, I <sub>B</sub> =0.5A					
		I <sub>C</sub> =5A, I <sub>B</sub> =0.8A					
		I <sub>C</sub> =6A, I <sub>B</sub> =1.2A					